

CLAIMS

1. A polishing composition to be used for polishing both surfaces of a semiconductor substrate, comprising silicon dioxide, a nitrogen-containing water-soluble polymer, and a basic compound, wherein

the silicon dioxide has an average primary particle diameter of 40 nm or more as calculated from the specific surface area determined by the BET method, and

the value of B/A is 1 or more and 447 or less and the value of C/A is 5,000 or more and 109,000 or less when in one liter of the polishing composition, A is defined as the number of silicon dioxide, B is defined as the number of monomer units of the nitrogen-containing water-soluble polymer, and C is defined as the number of molecules of the basic compound.

2. The polishing composition according to claim 1, wherein the nitrogen-containing water-soluble polymer has a weight average molecular weight of less than 1,500,000.

3. The polishing composition according to claim 1 or 2, wherein the silicon dioxide has true specific gravity of 1.7 or more.

4. The polishing composition according to any one of claims 1 to 3, wherein the basic compound includes a potassium compound and a quaternary ammonium compound.

5. A method for producing a semiconductor substrate, comprising polishing a semiconductor substrate as an object to be polished with the polishing composition according to any one of claims 1 to 4.